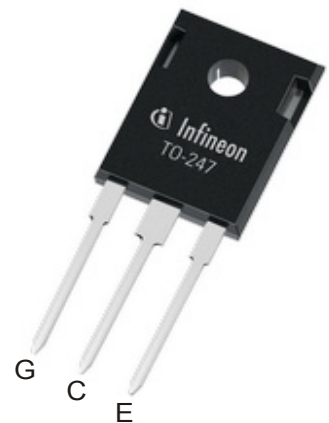
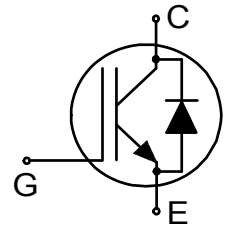


Sixth generation, high speed soft switching series

High speed soft switching TRENCHSTOP™ IGBT 6 in Trench and Fieldstop technology copacked with soft and fast recovery anti-parallel diode

Features:

- 1200V TRENCHSTOP™ IGBT6 technology offering:
- High efficiency in hard switching and resonant topologies
 - Easy paralleling capability due to positive temperature coefficient in V_{CEsat}
 - Low EMI
 - Low Gate Charge Q_g
 - Very soft, fast recovery anti-parallel diode
 - Maximum junction temperature 175°C
 - Pb-free lead plating; RoHS compliant
 - Complete product spectrum and PSpice Models:
<http://www.infineon.com/igbt/>



Applications:

- Industrial UPS
- Charger
- Energy storage
- Three-level Solar String Inverter
- Welding

Product Validation:

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22



Key Performance and Package Parameters

| Type | V_{CE} | I_C | $V_{CEsat}, T_{vj}=25^\circ\text{C}$ | T_{vjmax} | Marking | Package |
|--------------|----------|-------|--------------------------------------|-------------|---------|------------|
| IKW15N120BH6 | 1200V | 15A | 1.9V | 175°C | K15MBH6 | PG-TO247-3 |

Sixth generation, high speed soft switching series

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Sixth generation, high speed soft switching series

Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

| Parameter | Symbol | Value | Unit |
|---|-------------|----------------|--------------------|
| Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$ | V_{CE} | 1200 | V |
| DC collector current, limited by T_{vjmax} $T_c = 25^{\circ}\text{C}$ $T_c = 100^{\circ}\text{C}$ | I_C | 30.0 15.0 | A |
| Pulsed collector current, t_p limited by T_{vjmax} | I_{Cpuls} | 60.0 | A |
| Turn off safe operating area $V_{CE} \leq 1200\text{V}$, $T_{vj} \leq 175^{\circ}\text{C}$ | - | 60.0 | A |
| Diode forward current, limited by T_{vjmax} $T_c = 25^{\circ}\text{C}$ $T_c = 100^{\circ}\text{C}$ | I_F | 15.0 7.5 | A |
| Diode pulsed current, t_p limited by T_{vjmax} | I_{Fpuls} | 60.0 | A |
| Gate-emitter voltage Transient Gate-emitter voltage ($t_p \leq 0.5\mu\text{s}$, $D < 0.001$) | V_{GE} | ± 20 25 | V |
| Short circuit withstand time $V_{GE} = 15.0\text{V}$, $V_{CC} \leq 500\text{V}$ Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0\text{s}$ $T_{vj} = 150^{\circ}\text{C}$ | t_{SC} | 3 | μs |
| Power dissipation $T_c = 25^{\circ}\text{C}$ Power dissipation $T_c = 100^{\circ}\text{C}$ | P_{tot} | 200.0 100.0 | W |
| Operating junction temperature | T_{vj} | -40...+175 | $^{\circ}\text{C}$ |
| Storage temperature | T_{stg} | -55...+150 | $^{\circ}\text{C}$ |
| Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s | | 260 | $^{\circ}\text{C}$ |
| Mounting torque, M3 screw Maximum of mounting processes: 3 | M | 0.6 | Nm |

Thermal Resistance

| Parameter | Symbol | Conditions | Value | | | Unit |
|--|---------------|------------|-------|------|------|------|
| | | | min. | typ. | max. | |
| R_{th} Characteristics | | | | | | |
| IGBT thermal resistance, junction - case | $R_{th(j-c)}$ | | - | - | 0.74 | K/W |
| Diode thermal resistance, junction - case | $R_{th(j-c)}$ | | - | - | 2.40 | K/W |
| Thermal resistance junction - ambient | $R_{th(j-a)}$ | | - | - | 40 | K/W |

Sixth generation, high speed soft switching series

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | | | Unit |
|--------------------------------------|--------------|---|-------------|----------------------|----------------|---------------|
| | | | min. | typ. | max. | |
| Static Characteristic | | | | | | |
| Collector-emitter saturation voltage | V_{CEsat} | $V_{GE} = 15.0\text{V}$, $I_C = 15.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$ | - - - | 1.90 2.20 2.35 | 2.30 - - | V |
| Diode forward voltage | V_F | $V_{GE} = 0\text{V}$, $I_F = 7.5\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$ | - - | 2.00 2.00 | 2.40 - | V |
| Diode forward voltage | V_F | $V_{GE} = 0\text{V}$, $I_F = 15.0\text{A}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$ | - - | 2.65 2.75 | 3.20 - | V |
| Gate-emitter threshold voltage | $V_{GE(th)}$ | $I_C = 0.50\text{mA}$, $V_{CE} = V_{GE}$ | 5.1 | 5.7 | 6.3 | V |
| Zero gate voltage collector current | I_{CES} | $V_{CE} = 1200\text{V}$, $V_{GE} = 0\text{V}$ $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 175^{\circ}\text{C}$ | - - | - 450 | 250 - | μA |
| Gate-emitter leakage current | I_{GES} | $V_{CE} = 0\text{V}$, $V_{GE} = 20\text{V}$ | - | - | 600 | nA |
| Transconductance | g_{fs} | $V_{CE} = 20\text{V}$, $I_C = 15.0\text{A}$ | - | 10.0 | - | S |

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | | | Unit |
|--|-----------|--|-------|------|------|------|
| | | | min. | typ. | max. | |
| Dynamic Characteristic | | | | | | |
| Input capacitance | C_{ies} | $V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$ | - | 860 | - | pF |
| Output capacitance | C_{oes} | | - | 60 | - | |
| Reverse transfer capacitance | C_{res} | | - | 40 | - | |
| Gate charge | Q_G | $V_{CC} = 960\text{V}$, $I_C = 15.0\text{A}$, $V_{GE} = 15\text{V}$ | - | 92.0 | - | nC |
| Internal emitter inductance measured 5mm (0.197 in.) from case | L_E | | - | 13.0 | - | nH |

Switching Characteristic, Inductive Load

| Parameter | Symbol | Conditions | Value | | | Unit |
|---|--------------|--|-------|------|------|------|
| | | | min. | typ. | max. | |
| IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$ | | | | | | |
| Turn-on delay time | $t_{d(on)}$ | $T_{vj} = 25^{\circ}\text{C}$, $V_{CC} = 600\text{V}$, $I_C = 15.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $R_{G(on)} = 22.0\Omega$, $R_{G(off)} = 22.0\Omega$, $L\sigma = 95\text{nH}$, $C\sigma = 67\text{pF}$ $L\sigma$, $C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery. | - | 18 | - | ns |
| Rise time | t_r | | - | 29 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 240 | - | ns |
| Fall time | t_f | | - | 25 | - | ns |
| Turn-on energy | E_{on} | | - | 0.70 | - | mJ |
| Turn-off energy | E_{off} | | - | 0.55 | - | mJ |
| Total switching energy | E_{ts} | | - | 1.25 | - | mJ |

Sixth generation, high speed soft switching series

Diode Characteristic, at $T_{vj} = 25^{\circ}\text{C}$

| | | | | | | |
|--|--------------|---|---|------|---|------------------------|
| Diode reverse recovery time | t_{rr} | $T_{vj} = 25^{\circ}\text{C}$, $V_R = 600\text{V}$, $I_F = 15.0\text{A}$, $di_F/dt = 500\text{A}/\mu\text{s}$, $L\sigma = 95\text{nH}$, $C\sigma = 67\text{pF}$ | - | 340 | - | ns |
| Diode reverse recovery charge | Q_{rr} | | - | 0.83 | - | μC |
| Diode peak reverse recovery current | I_{rrm} | | - | 8.3 | - | A |
| Diode peak rate of fall of reverse recovery current during t_b | di_{rr}/dt | | - | -55 | - | $\text{A}/\mu\text{s}$ |

Switching Characteristic, Inductive Load

| Parameter | Symbol | Conditions | Value | | | Unit |
|-----------|--------|------------|-------|------|------|------|
| | | | min. | typ. | max. | |

IGBT Characteristic, at $T_{vj} = 175^{\circ}\text{C}$

| | | | | | | |
|------------------------|--------------|--|---|------|---|----|
| Turn-on delay time | $t_{d(on)}$ | $T_{vj} = 175^{\circ}\text{C}$, $V_{CC} = 600\text{V}$, $I_C = 15.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $R_{G(on)} = 22.0\Omega$, $R_{G(off)} = 22.0\Omega$, $L\sigma = 95\text{nH}$, $C\sigma = 67\text{pF}$ $L\sigma$, $C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery. | - | 17 | - | ns |
| Rise time | t_r | | - | 29 | - | ns |
| Turn-off delay time | $t_{d(off)}$ | | - | 310 | - | ns |
| Fall time | t_f | | - | 63 | - | ns |
| Turn-on energy | E_{on} | | - | 0.95 | - | mJ |
| Turn-off energy | E_{off} | | - | 1.10 | - | mJ |
| Total switching energy | E_{ts} | | - | 2.05 | - | mJ |

Diode Characteristic, at $T_{vj} = 175^{\circ}\text{C}$

| | | | | | | |
|--|--------------|--|---|------|---|------------------------|
| Diode reverse recovery time | t_{rr} | $T_{vj} = 175^{\circ}\text{C}$, $V_R = 600\text{V}$, $I_F = 15.0\text{A}$, $di_F/dt = 500\text{A}/\mu\text{s}$, $L\sigma = 95\text{nH}$, $C\sigma = 67\text{pF}$ | - | 540 | - | ns |
| Diode reverse recovery charge | Q_{rr} | | - | 1.75 | - | μC |
| Diode peak reverse recovery current | I_{rrm} | | - | 11.3 | - | A |
| Diode peak rate of fall of reverse recovery current during t_b | di_{rr}/dt | | - | -42 | - | $\text{A}/\mu\text{s}$ |

Sixth generation, high speed soft switching series

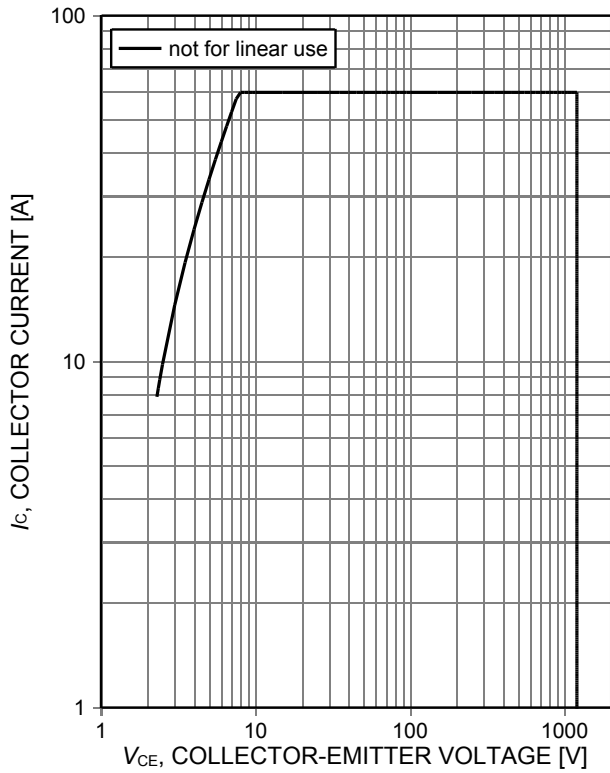


Figure 1. **Forward bias safe operating area**
 ($D=0$, $T_{vj} \leq 175^\circ\text{C}$; $V_{GE}=15\text{V}$, pulse width limited by T_{vjmax})

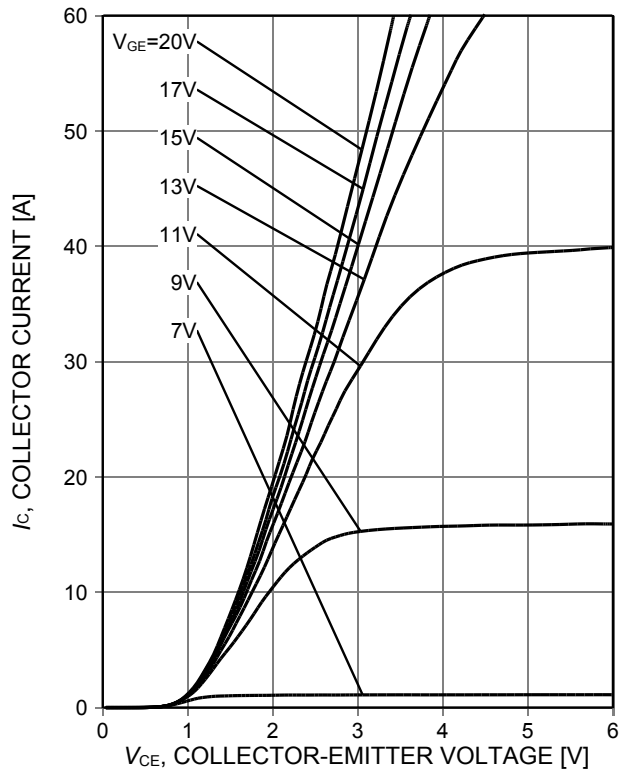


Figure 2. **Typical output characteristic**
 ($T_{vj}=25^\circ\text{C}$)

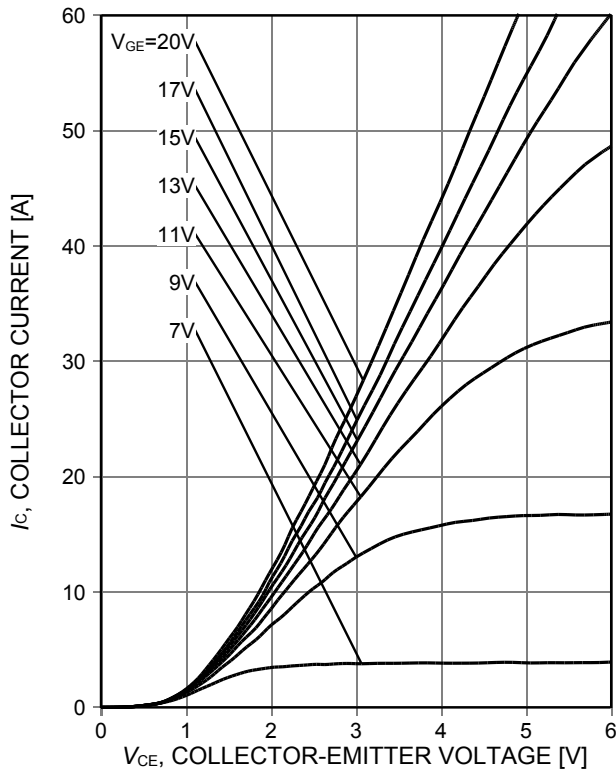


Figure 3. **Typical output characteristic**
 ($T_{vj}=175^\circ\text{C}$)

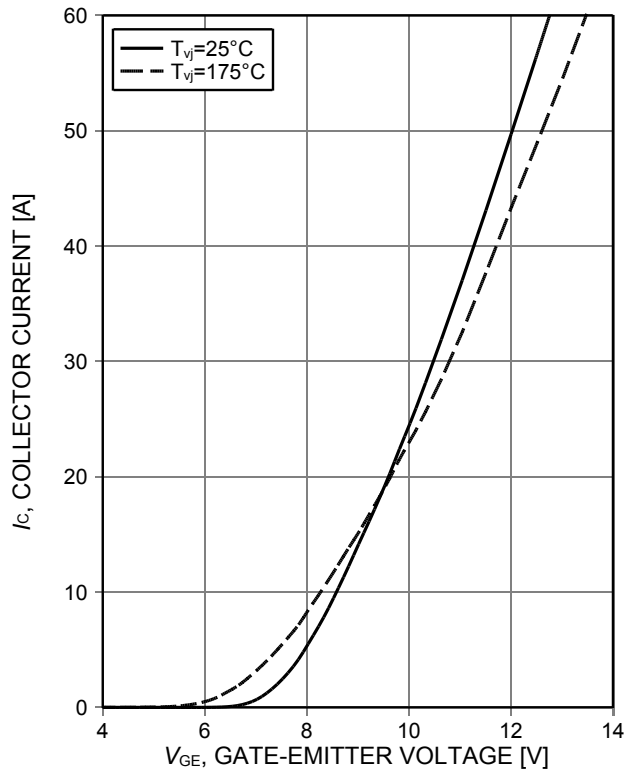


Figure 4. **Typical transfer characteristic**
 ($V_{CE}=20\text{V}$)

Sixth generation, high speed soft switching series

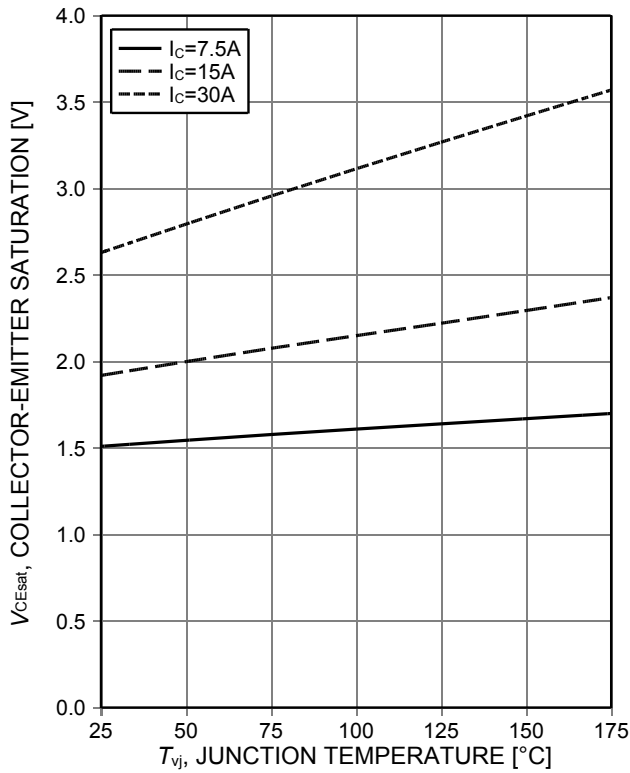


Figure 5. Typical collector-emitter saturation voltage as a function of junction temperature ($V_{GE}=15V$)

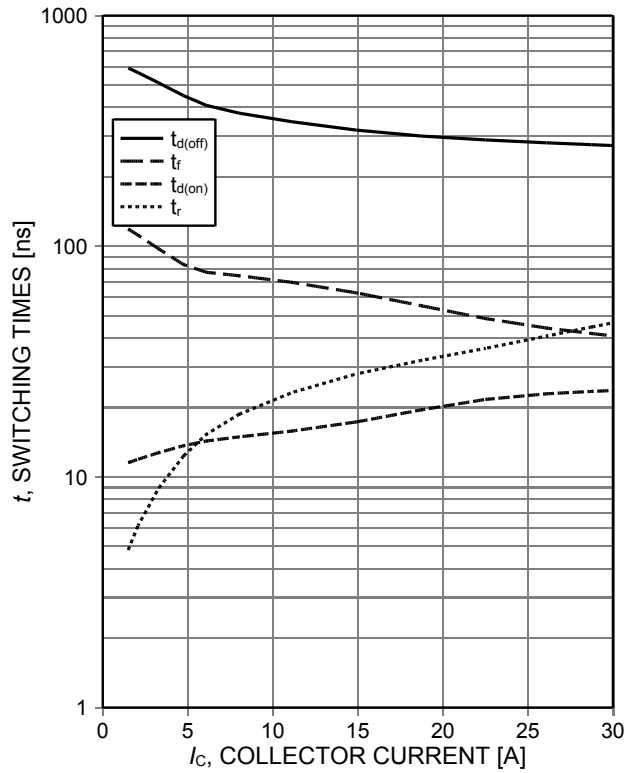


Figure 6. Typical switching times as a function of collector current (inductive load, $T_{vj}=175^{\circ}C$, $V_{CE}=600V$, $V_{GE}=15/0V$, $R_G=22\Omega$, Dynamic test circuit in Figure E)

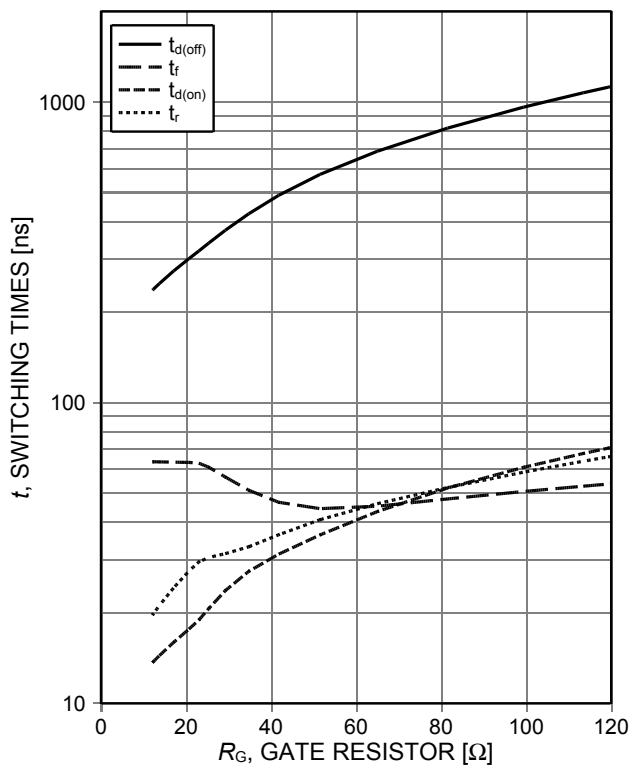


Figure 7. Typical switching times as a function of gate resistor (inductive load, $T_{vj}=175^{\circ}C$, $V_{CE}=600V$, $V_{GE}=15/0V$, $I_c=15A$, Dynamic test circuit in Figure E)

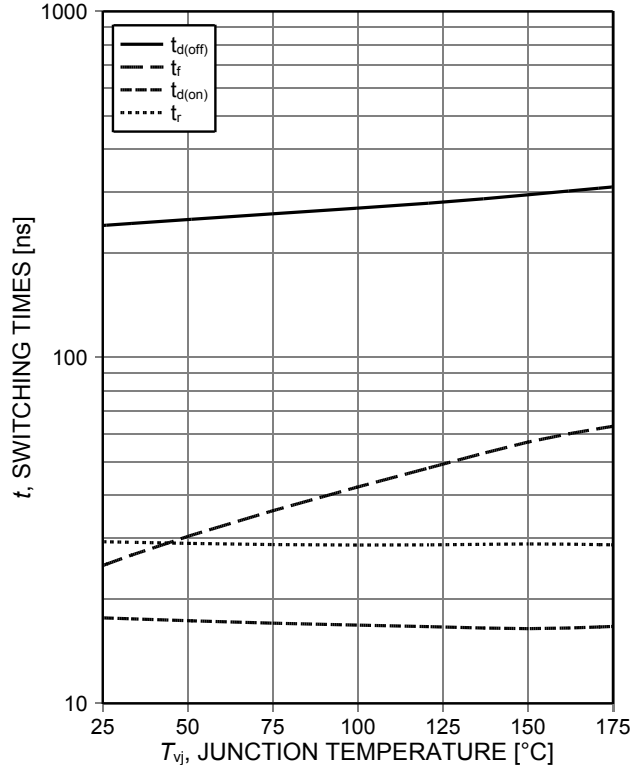


Figure 8. Typical switching times as a function of junction temperature (inductive load, $V_{CE}=600V$, $V_{GE}=15/0V$, $I_c=15A$, $R_G=22\Omega$, Dynamic test circuit in Figure E)

Sixth generation, high speed soft switching series

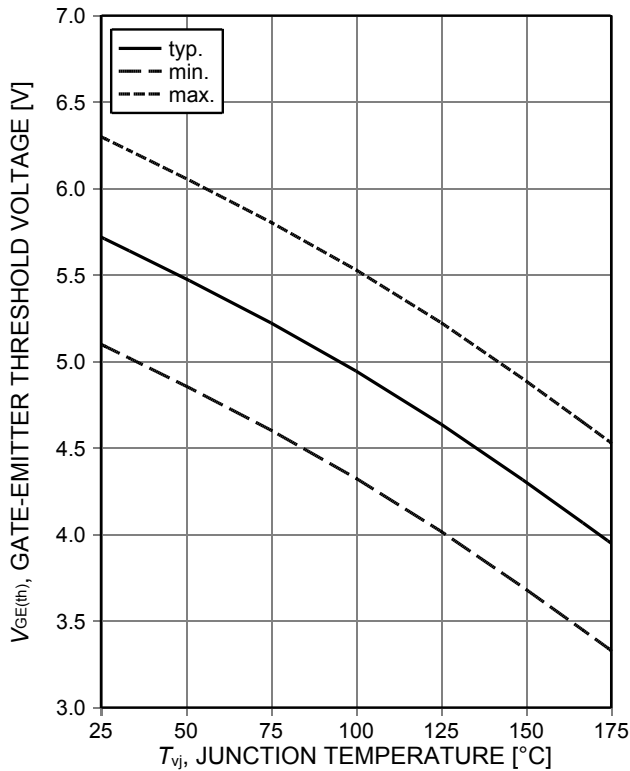


Figure 9. Gate-emitter threshold voltage as a function of junction temperature ($I_C=0.5mA$)

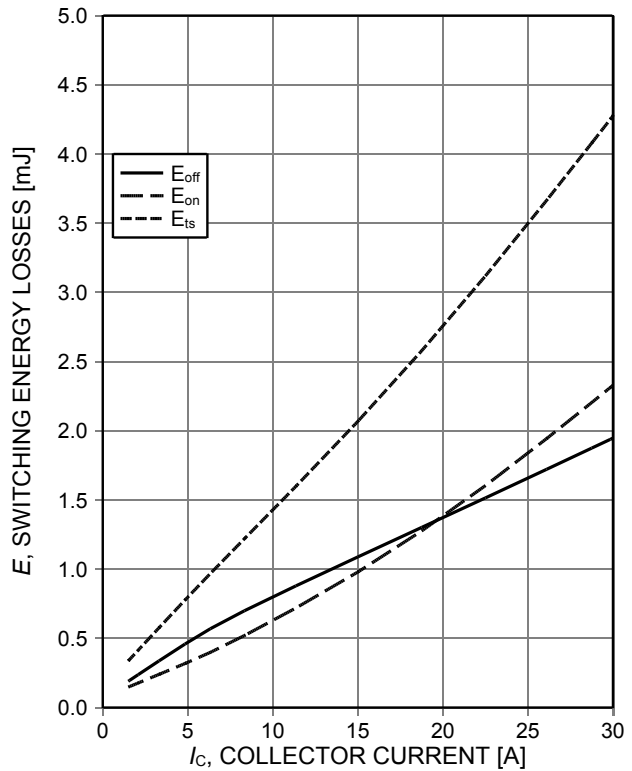


Figure 10. Typical switching energy losses as a function of collector current (inductive load, $T_{vj}=175^{\circ}C$, $V_{CE}=600V$, $V_{GE}=15/0V$, $R_G=22\Omega$, Dynamic test circuit in Figure E)

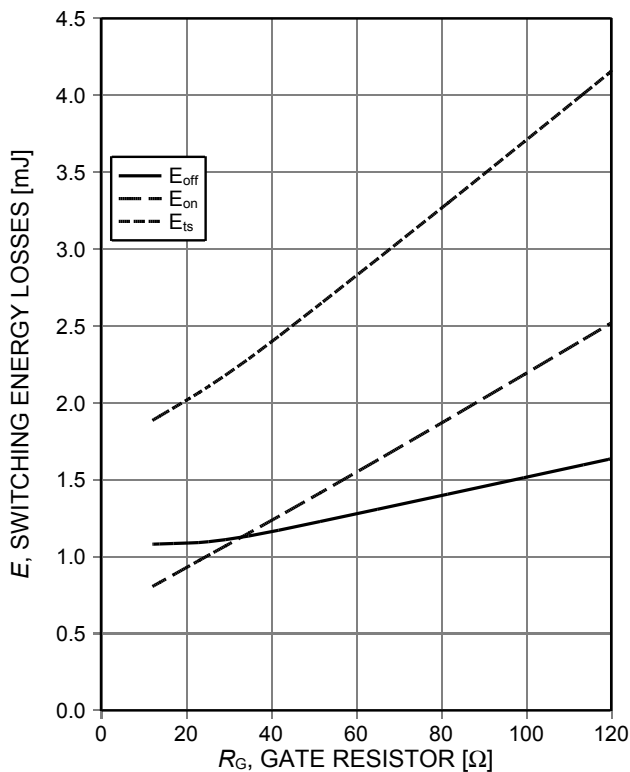


Figure 11. Typical switching energy losses as a function of gate resistor (inductive load, $T_{vj}=175^{\circ}C$, $V_{CE}=600V$, $V_{GE}=15/0V$, $I_C=15A$, Dynamic test circuit in Figure E)

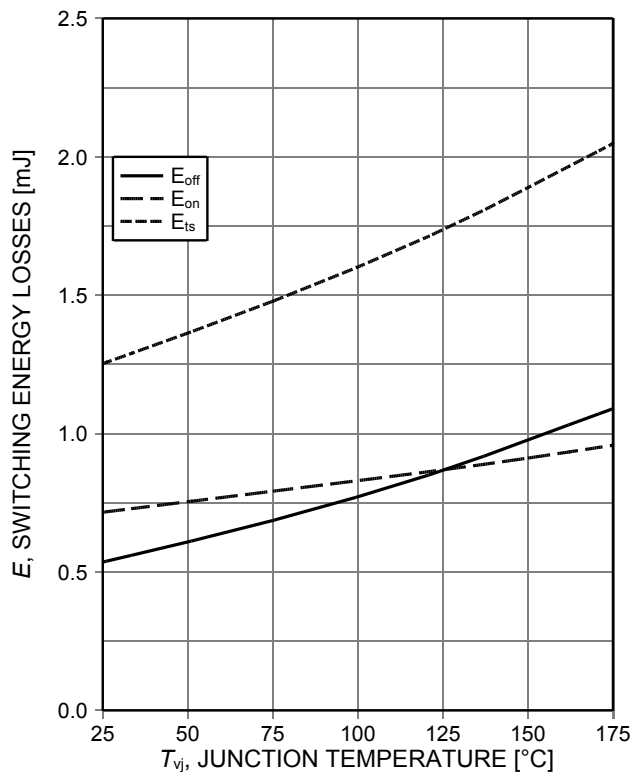


Figure 12. Typical switching energy losses as a function of junction temperature (inductive load, $V_{CE}=600V$, $V_{GE}=15/0V$, $I_C=15A$, $R_G=22\Omega$, Dynamic test circuit in Figure E)

Sixth generation, high speed soft switching series

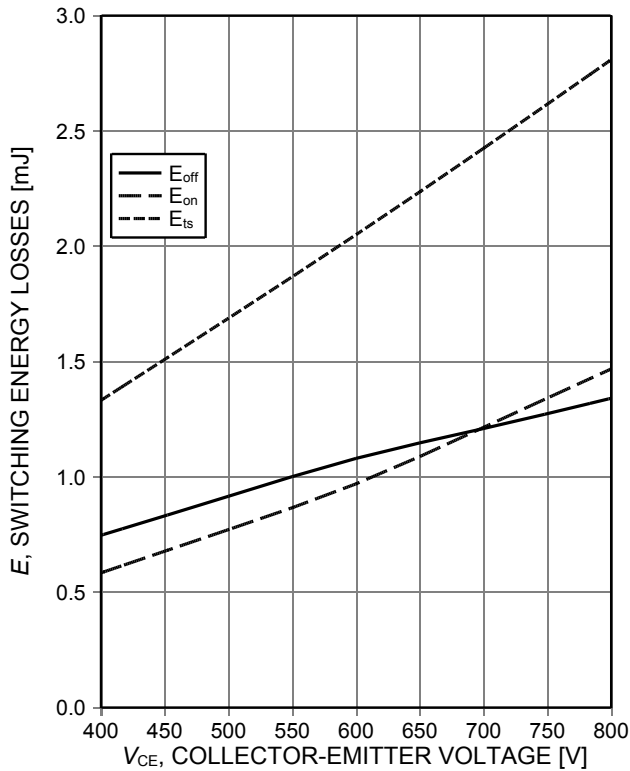


Figure 13. **Typical switching energy losses as a function of collector emitter voltage** (inductive load, $T_{vj}=175^{\circ}\text{C}$, $V_{GE}=15/0\text{V}$, $I_C=15\text{A}$, $R_G=22\Omega$, Dynamic test circuit in Figure E)

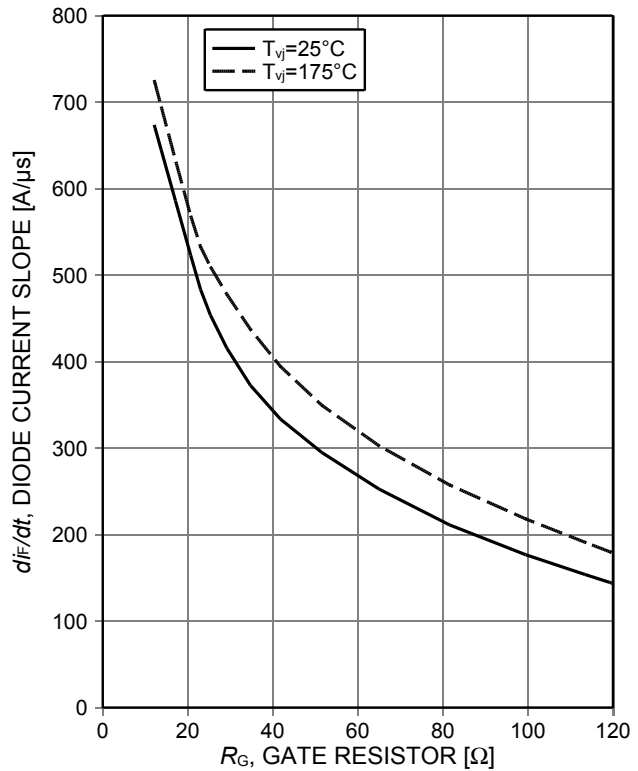


Figure 14. **Typical diode current slope as a function of gate resistor** (inductive load, $V_{CE}=600\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=40\text{A}$, Dynamic test circuit in Figure E)

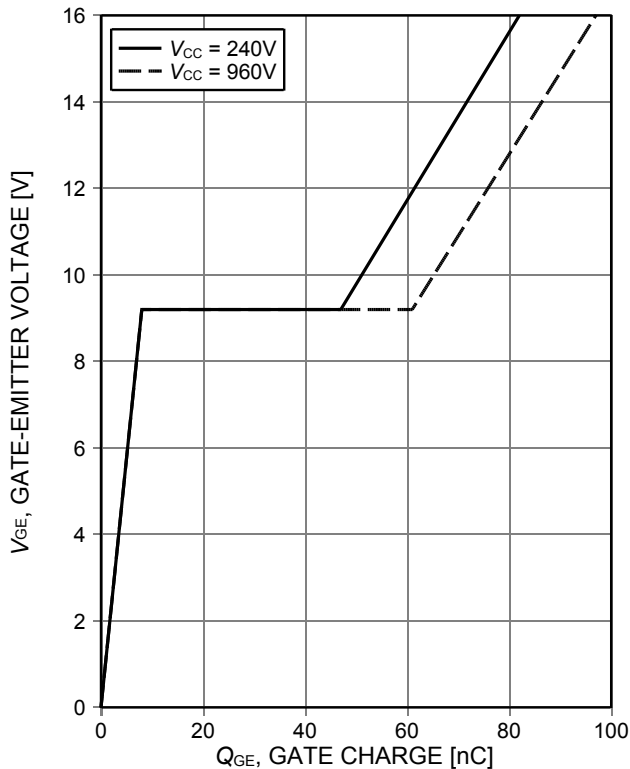


Figure 15. **Typical gate charge** ($I_C=15\text{A}$)

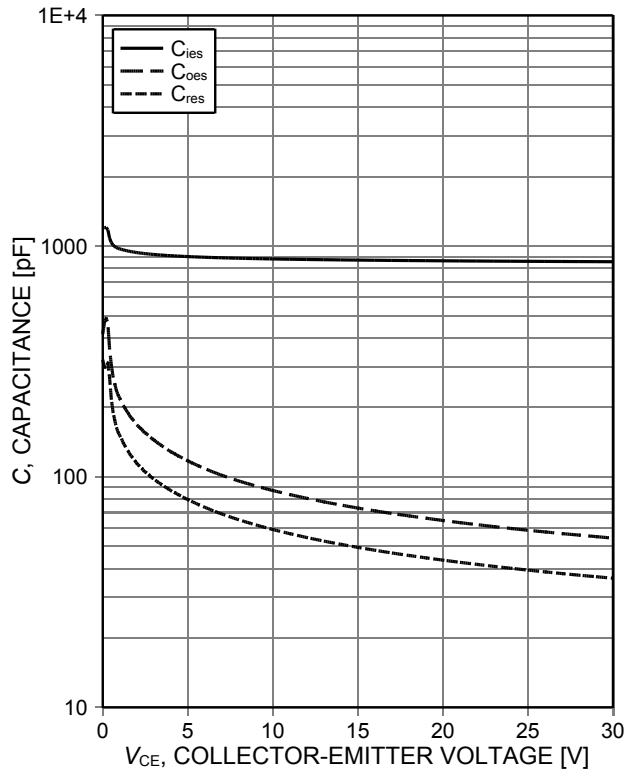


Figure 16. **Typical capacitance as a function of collector-emitter voltage** ($V_{GE}=0\text{V}$, $f=1\text{MHz}$)

Sixth generation, high speed soft switching series

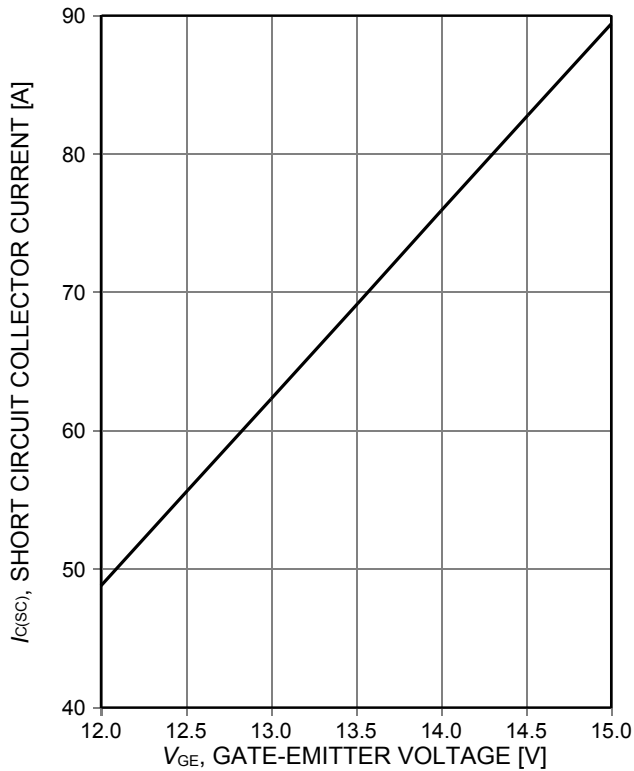


Figure 17. Typical short circuit collector current as a function of gate-emitter voltage (V_{CE}≤500V, T_{vj}≤150°C)

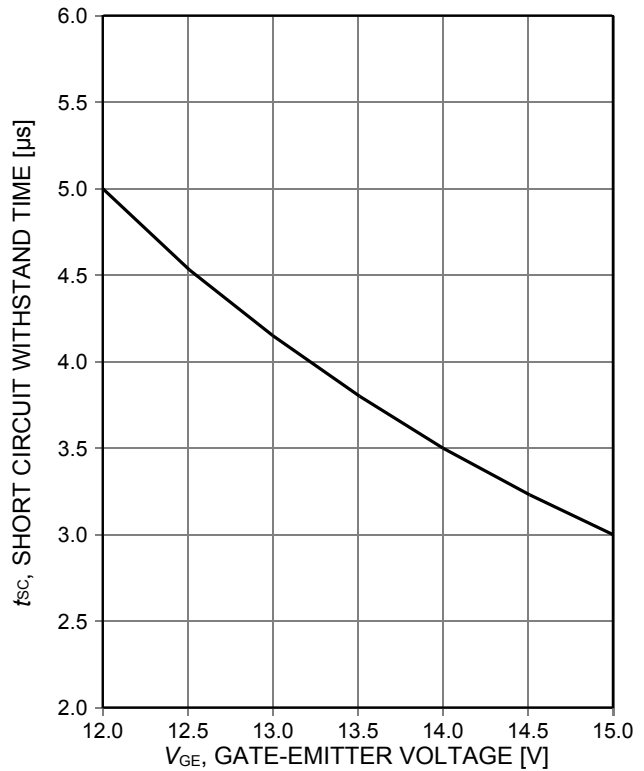


Figure 18. Short circuit withstand time as a function of gate-emitter voltage (V_{CE}≤500V, start at T_{vj}≤150°C)

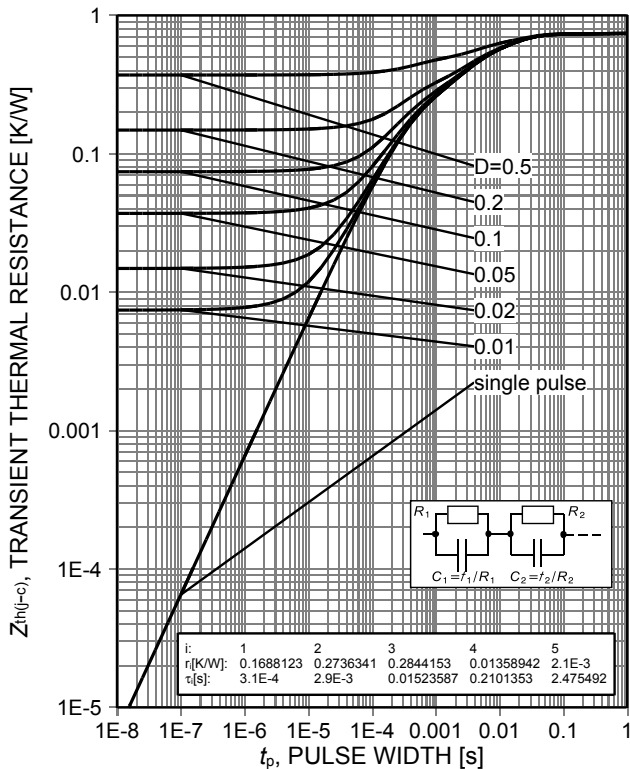


Figure 19. IGBT transient thermal resistance (D=t_p/T)

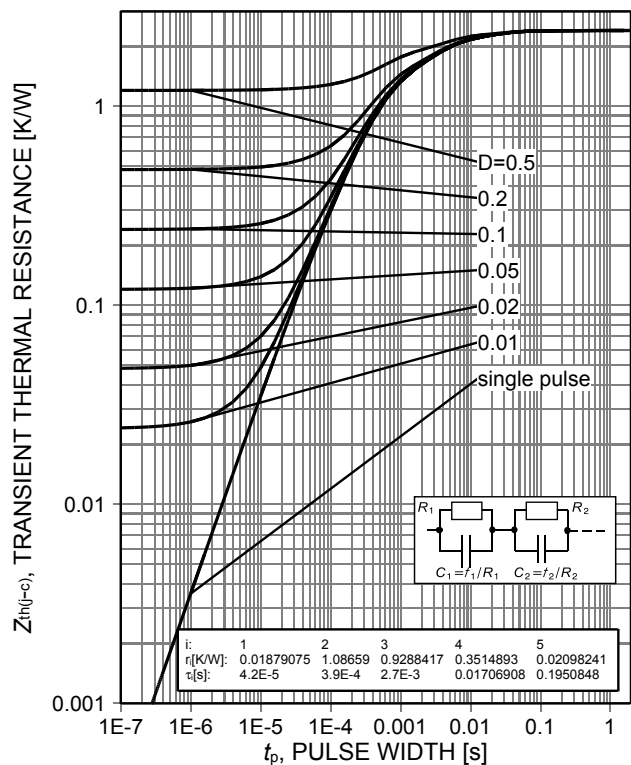


Figure 20. Diode transient thermal impedance as a function of pulse width (D=t_p/T)

Sixth generation, high speed soft switching series

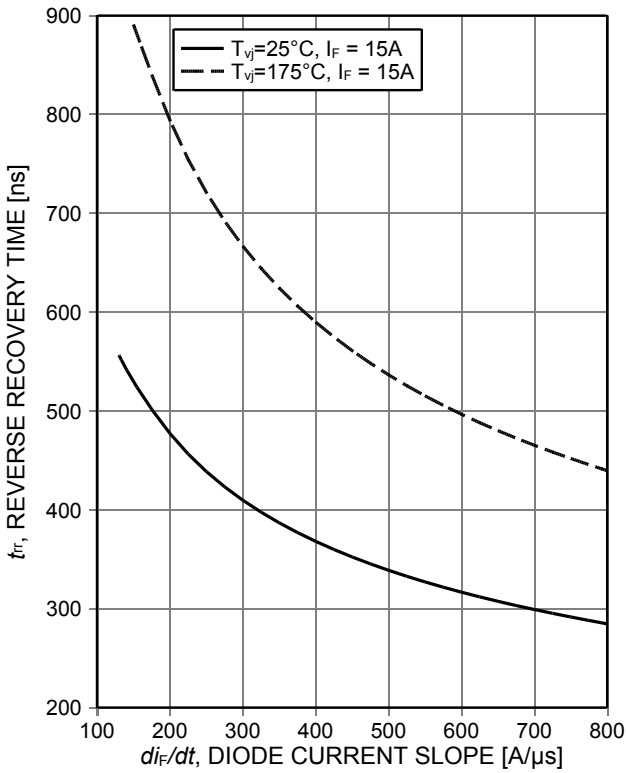


Figure 21. Typical reverse recovery time as a function of diode current slope ($V_R=600V$)

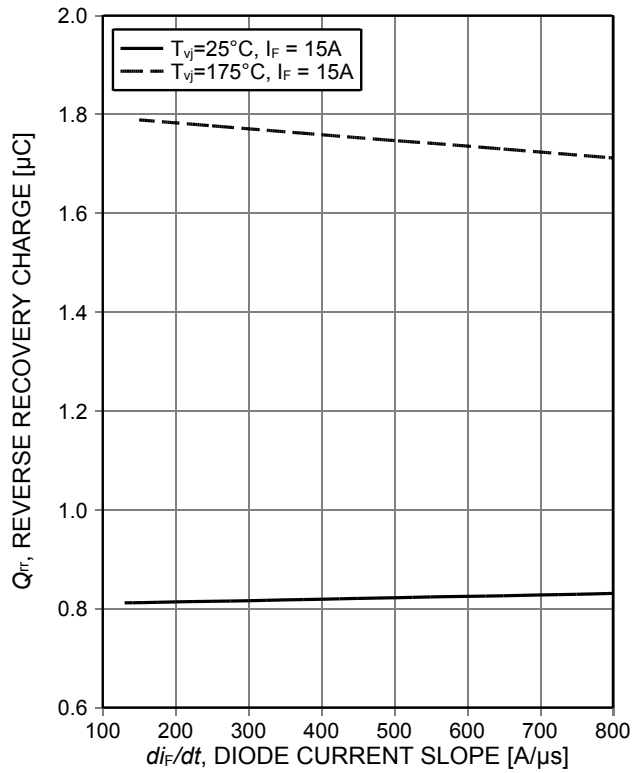


Figure 22. Typical reverse recovery charge as a function of diode current slope ($V_R=600V$)

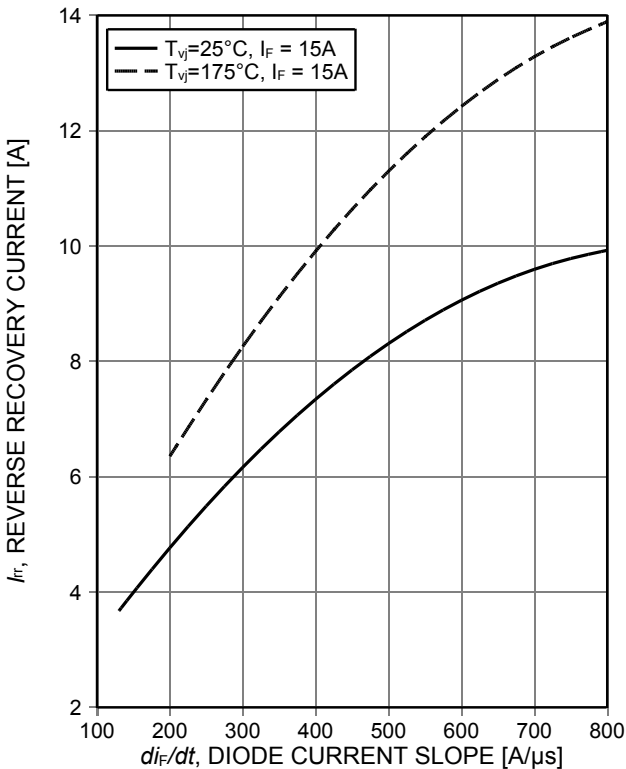


Figure 23. Typical reverse recovery current as a function of diode current slope ($V_R=600V$)

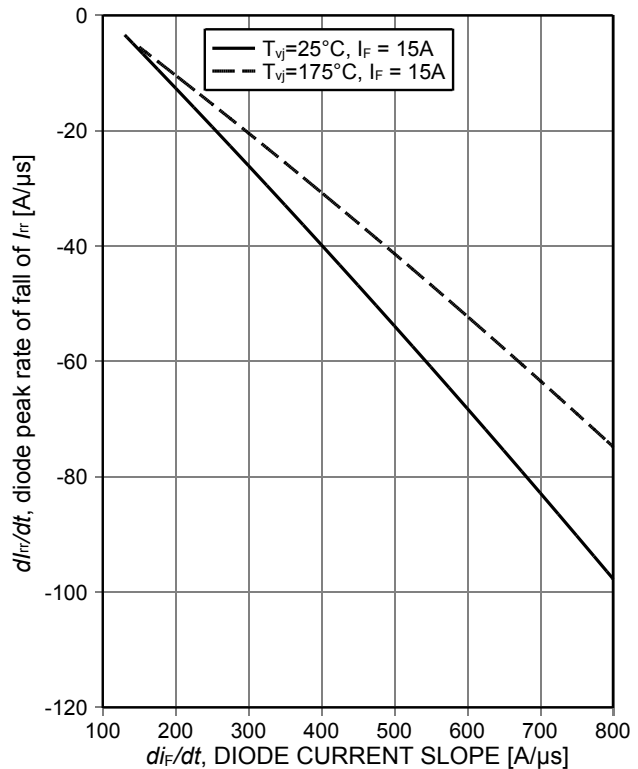


Figure 24. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope ($V_R=600V$)

Sixth generation, high speed soft switching series

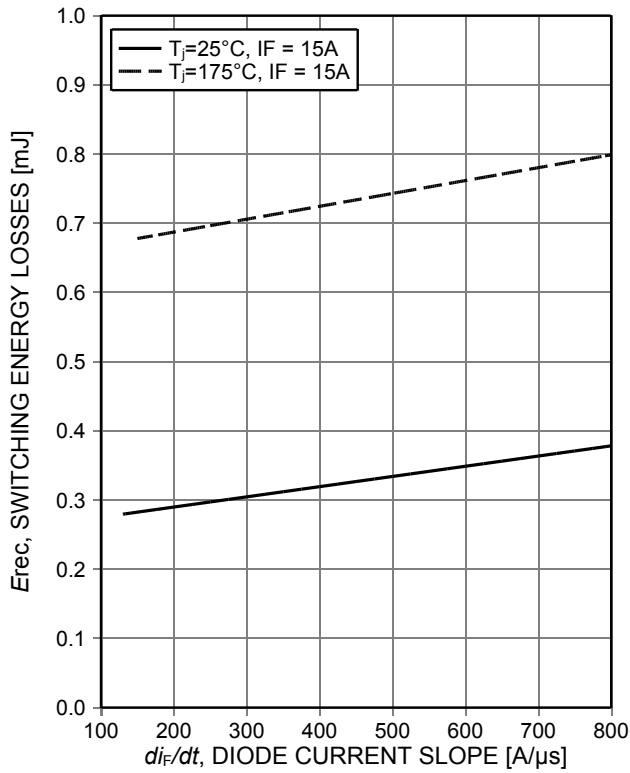


Figure 25. Typical reverse energy losses as a function of diode current slope (V_R=600V)

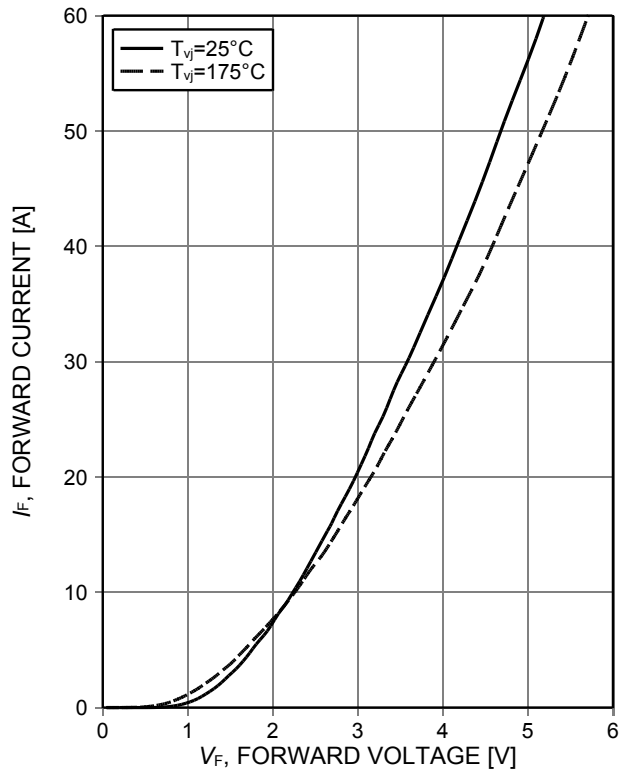


Figure 26. Typical diode forward current as a function of forward voltage

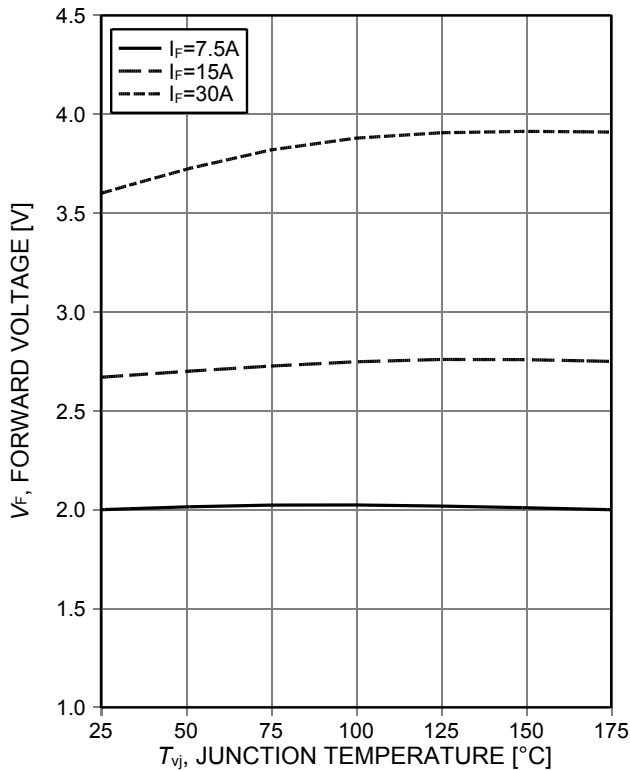
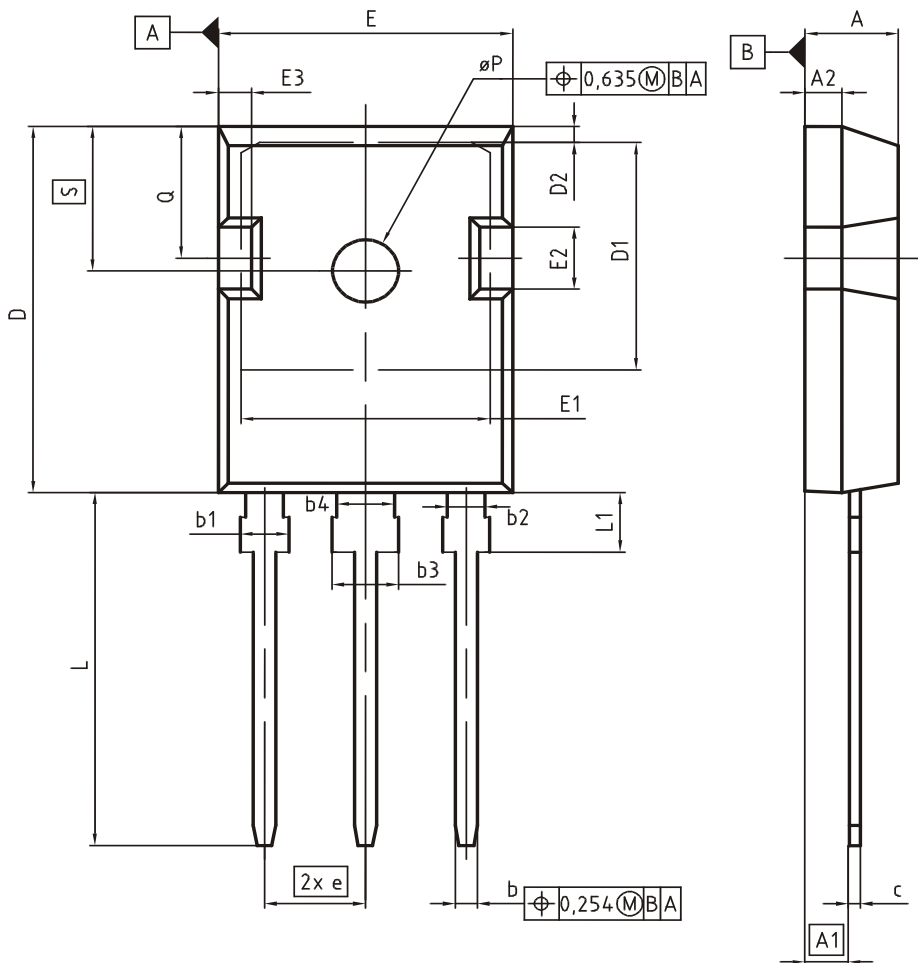


Figure 27. Typical diode forward voltage as a function of junction temperature

Sixth generation, high speed soft switching series

Package Drawing PG-TO247-3



| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.83 | 5.21 | 0.190 | 0.205 |
| A1 | 2.27 | 2.54 | 0.089 | 0.100 |
| A2 | 1.85 | 2.16 | 0.073 | 0.085 |
| b | 1.07 | 1.33 | 0.042 | 0.052 |
| b1 | 1.90 | 2.41 | 0.075 | 0.095 |
| b2 | 1.90 | 2.16 | 0.075 | 0.085 |
| b3 | 2.87 | 3.38 | 0.113 | 0.133 |
| b4 | 2.87 | 3.13 | 0.113 | 0.123 |
| c | 0.55 | 0.68 | 0.022 | 0.027 |
| D | 20.80 | 21.10 | 0.819 | 0.831 |
| D1 | 16.25 | 17.65 | 0.640 | 0.695 |
| D2 | 0.95 | 1.35 | 0.037 | 0.053 |
| E | 15.70 | 16.13 | 0.618 | 0.635 |
| E1 | 13.10 | 14.15 | 0.516 | 0.557 |
| E2 | 3.68 | 5.10 | 0.145 | 0.201 |
| E3 | 1.00 | 2.60 | 0.039 | 0.102 |
| e | 5.44 (BSC) | | 0.214 (BSC) | |
| N | 3 | | 3 | |
| L | 19.80 | 20.32 | 0.780 | 0.800 |
| L1 | 4.10 | 4.47 | 0.161 | 0.176 |
| øP | 3.50 | 3.70 | 0.138 | 0.146 |
| Q | 5.49 | 6.00 | 0.216 | 0.236 |
| S | 6.04 | 6.30 | 0.238 | 0.248 |

DOCUMENT NO.
Z8B00003327

SCALE

EUROPEAN PROJECTION

ISSUE DATE
09-07-2010

REVISION
05

Testing Conditions



Figure A. Definition of switching times



Figure B. Definition of switching losses

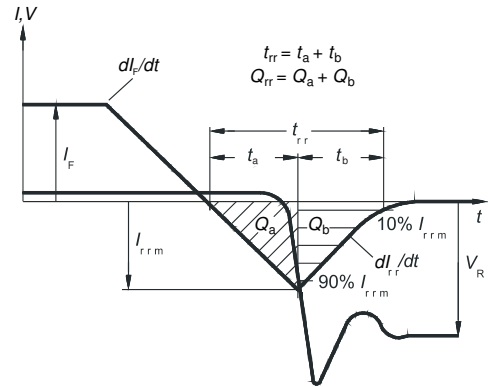


Figure C. Definition of diode switching characteristics

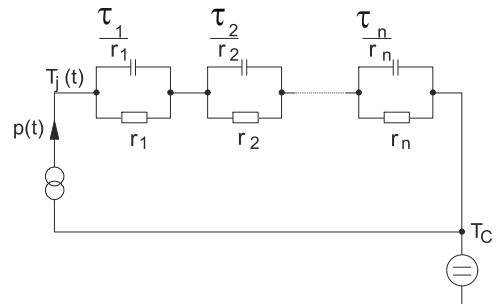


Figure D. Thermal equivalent circuit



Figure E. Dynamic test circuit
Parasitic inductance L_{σ} ,
parasitic capacitor C_{σ} ,
relief capacitor C_r ,
(only for ZVT switching)

Sixth generation, high speed soft switching series

Revision History

IKW15N120BH6

Revision: 2018-05-07, Rev. 2.1

Previous Revision

| Revision | Date | Subjects (major changes since last revision) |
|----------|------------|--|
| 2.1 | 2018-05-07 | Final data sheet |

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Infineon Technologies AG
81726 München, Germany
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